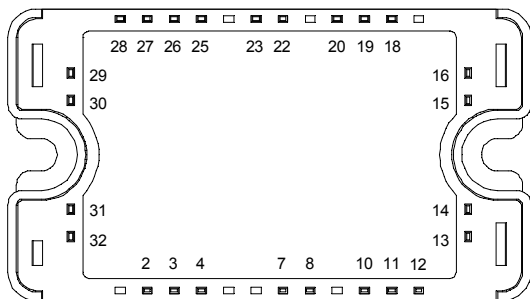
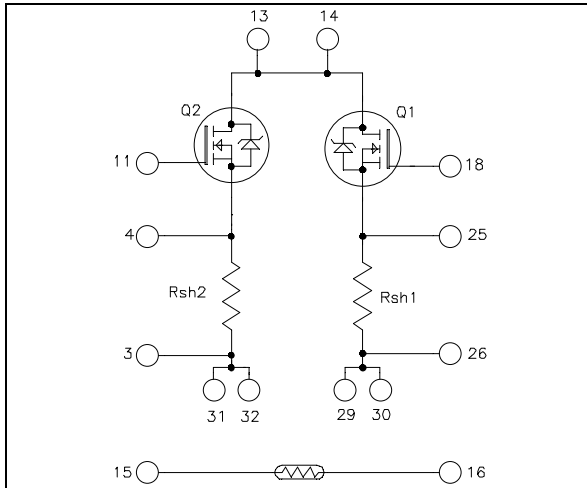


Linear MOSFET Power Module

$V_{DSS} = 100V$
 $R_{DSon} = 09m\Omega$ typ @ $T_j = 25^\circ C$
 $I_D = 154A^*$ @ $T_c = 25^\circ C$



Pins 13/14 ; 29/30 ; 31/32 must be shorted together

Application

- Electronic load dedicated to power supplies and battery discharge testing

Features

- Linear MOSFET
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration
- AlN substrate for improved thermal performance

Benefits

- Direct mounting to heatsink (isolated package)
- easy series and parallels combinations for power and voltage improvements
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings (per leg)

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	100	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	154*
		$T_c = 80^\circ C$	115*
I_{DM}	Pulsed Drain current	430	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	10	m Ω
P_D	Maximum Power Dissipation ①	$T_c = 25^\circ C$	480
I_{AR}	Avalanche current (repetitive and non repetitive)	100	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	3000	

* Output current per leg must be limited to 67A @ $T_c=25^\circ C$ and 47A @ $T_c=80^\circ C$ to not exceed the shunt specification. In addition the current capability must be limited to 75A on pins 13/14 to not exceed current capability of the pins.

① In saturation mode

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics (per leg)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0V, V _{DS} = 100V	T _j = 25°C			100	μA
		V _{GS} = 0V, V _{DS} = 80V	T _j = 125°C			500	
R _{DS(on)}	Drain – Source on Resistance	V _{GS} = 10V, I _D = 69.5A			9	10	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 2.5mA		2		4	V
I _{GSS}	Gate – Source Leakage Current	V _{GS} = ±30 V, V _{DS} = 0V				±100	nA

Dynamic Characteristics (per leg)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C _{iss}	Input Capacitance	V _{GS} = 0V		9875		pF
C _{oss}	Output Capacitance	V _{DS} = 25V		3940		
C _{rss}	Reverse Transfer Capacitance	f = 1MHz		1470		

Shunt Electrical Characteristics (per leg)

Symbol	Characteristic	Min	Typ	Max	Unit
R _{sh}	Resistance value		4.4		mΩ
T _{sh}	Tolerance		2		%
P _{sh}	Load capacity	T _C =25°C		20	W
		T _C =80°C		10	
I _{sh}	Current capacity	T _C =25°C		67	A
		T _C =80°C		47	

Temperature sensor PTC

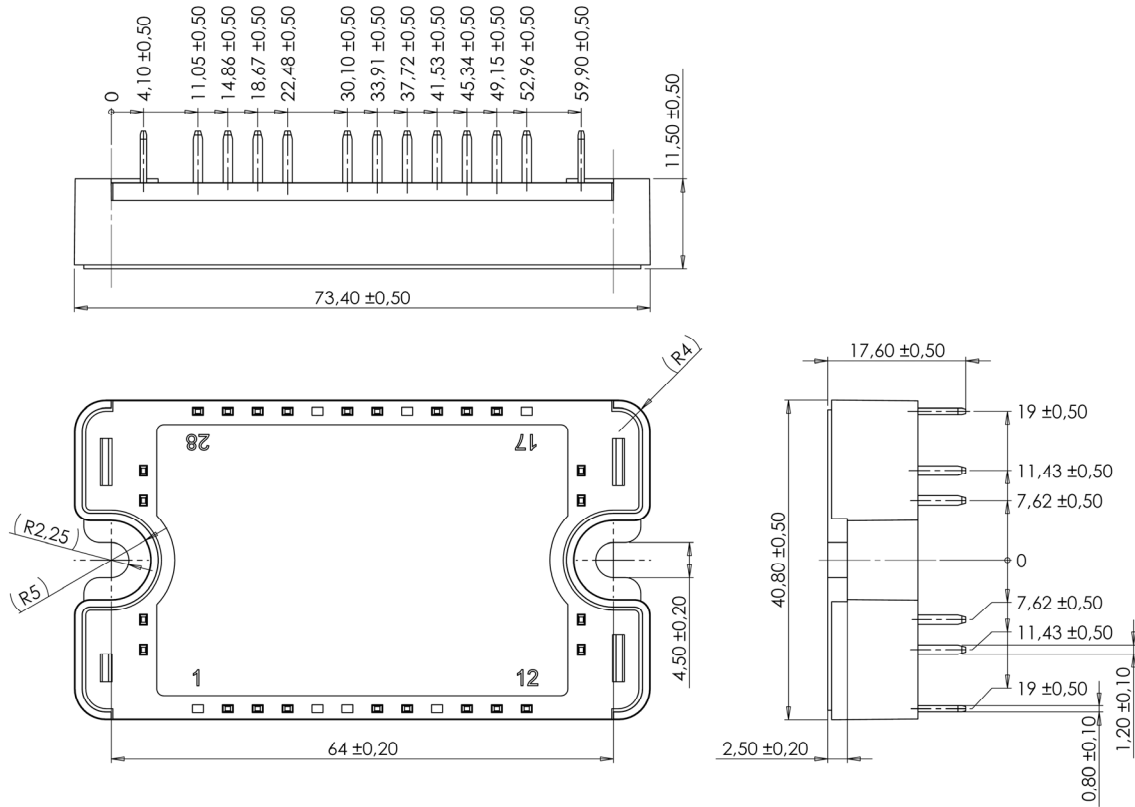
Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C	1980		2020	Ω
R ₁₀₀ /R ₂₅	Resistance ratio	T _{amb} =100°C & 25°C	1.676	1.696	1.716
R ₋₅₅ /R ₂₅	Resistance ratio	T _{amb} =-55°C & 25°C	0.48	0.49	0.50
B	Temperature coefficient		7900		ppm/K

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance	MOSFET (per leg)		0.26	°C/W	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

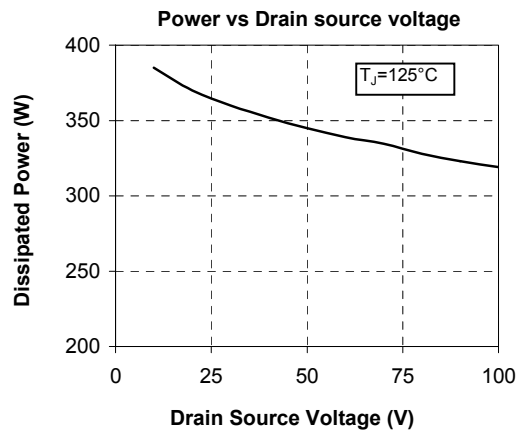
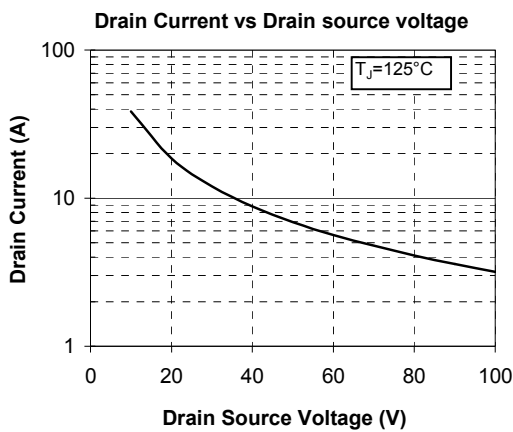


SP3 Package outline (dimensions in mm)



See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve (linear mode) (per leg)





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